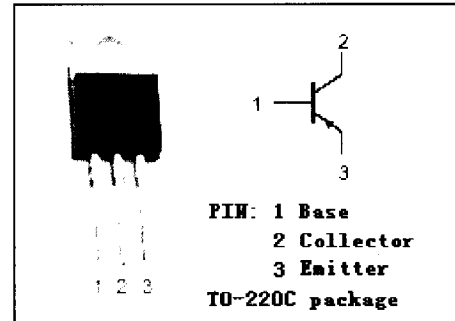


Silicon PNP Power Transistor

2SB919

DESCRIPTION

- High Collector Current: $I_C = -8A$
- Low Collector Saturation Voltage
 $V_{CE(sat)} = -0.5V(\text{Max}) @ I_C = -3A$
- Complement to Type 2SD1235

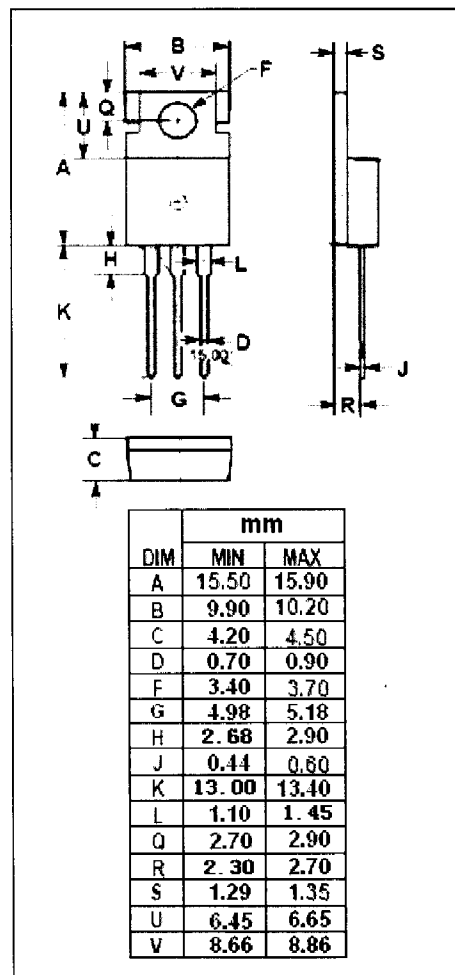


APPLICATIONS

- Designed for large current switching applications.

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-30	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-8	A
I_{CM}	Collector Current-Peak	-15	A
P_C	Total Power Dissipation @ $T_C = 25^\circ\text{C}$	30	W
	Total Power Dissipation @ $T_a = 25^\circ\text{C}$	1.75	
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.



Silicon PNP Power Transistor

2SB919

ELECTRICAL CHARACTERISTICS

$T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -1\text{mA}; R_{BE} = \infty$	-30			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = -1\text{mA}; I_E = 0$	-60			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = -1\text{mA}; I_C = 0$	-6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -3\text{A}; I_B = -0.15\text{A}$			-0.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -40\text{V}; I_E = 0$			-0.1	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -4\text{V}; I_C = 0$			-0.1	mA
h_{FE-1}	DC Current Gain	$I_C = -1\text{A}; V_{CE} = -2\text{V}$	70		280	
h_{FE-2}	DC Current Gain	$I_C = -4\text{A}; V_{CE} = -2\text{V}$	30			
f_T	Current-Gain—Bandwidth Product	$I_C = -1\text{A}; V_{CE} = -5\text{V}$		120		MHz

◆ h_{FE-1} Classifications

Q	R	S
70-140	100-200	140-280